

# 40 V, 200 mA NPN switching transistor Rev. 1 – 7 March 2012

Product data sheet

#### 1. **Product profile**

### **1.1 General description**

NPN single switching transistor in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

PNP complement: PMBT3906MB.

### **1.2 Features and benefits**

- Single general-purpose switching transistor
- AEC-Q101 qualified
- Ultra small SMD plastic package
- Board-space reduction
- Low package height of 0.37 mm

### 1.3 Applications

- General-purpose switching and amplification
- Mobile applications

### 1.4 Quick reference data

### Table 1 Ouick reference data

Table 1.	Quick reference uata						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
$V_{CEO}$	collector-emitter voltage	open base	-	-	40	V	
I <sub>C</sub>	collector current		-	-	200	mA	
h <sub>FE</sub>	DC current gain	$V_{CE} = 1 V;$ $I_{C} = 10 mA$	100	180	300		

#### **Pinning information** 2.

Pin	Description	Simplified outline Graphic symbol
1	base	
2	emitter	
3	collector	
		Transparent 2



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### 3. Ordering information

Table 3. Ordering	informatio	n	
Type number	Package		
	Name	Description	Version
PMBT3904MB		leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.37 mm	SOT883B

### 4. Marking

Table 4.   Marking codes	
Type number	Marking code <sup>[1]</sup>
PMBT3904MB	0100 0111

[1] For SOT883B binary marking code description see Figure 1.

### 4.1 Binary marking code description



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### 5. Limiting values

Table 5. In accorda	Limiting values nce with the Absolute Maximum Ra	ating System (IEC	60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	40	V
$V_{\text{EBO}}$	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	200	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[1][2]	250	mW
			<u>[1][3]</u>	590	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Reflow soldering is the only recommended soldering method.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

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### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	<u>[1][2]</u>	-	500	K/W
	junction to ambient		<u>[1][3]</u>	-	212	K/W

[1] Reflow soldering is the only recommended soldering method.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



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### 7. Characteristics

<b>Table 7.</b> $T_{amb} = 25$	Characteristics ℃ unless otherwise sp	ecified.					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 30 \text{ V}; \text{ I}_{E} = 0 \text{ A}$		-	-	50	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 6 V; I_C = 0 A$		-	-	50	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 1 V$					
		I <sub>C</sub> = 0.1 mA		60	180	-	
		$I_{\rm C} = 1  \rm{mA}$		80	180	-	
		I <sub>C</sub> = 10 mA		100	180	300	
		I <sub>C</sub> = 50 mA		60	105	-	
		I <sub>C</sub> = 100 mA	[1]	30	50	-	
V <sub>CEsat</sub>	collector-emitter	$I_{C} = 10 \text{ mA}; I_{B} = 1 \text{ mA}$		-	75	200	mV
saturation voltage		$I_{C} = 50 \text{ mA}; I_{B} = 5 \text{ mA}$		-	120	300	mV
V <sub>BEsat</sub> base-emitter saturation voltage	base-emitter	$I_{C} = 10 \text{ mA}; I_{B} = 1 \text{ mA}$		650	750	850	mV
	$I_{C} = 50 \text{ mA}; I_{B} = 5 \text{ mA}$		-	850	950	mV	
t <sub>d</sub>	delay time	$V_{CC} = 3 \text{ V}; I_{C} = 10 \text{ mA};$		-	-	35	ns
t <sub>r</sub>	rise time	$I_{Bon} = 1 \text{ mA};$		-	-	35	ns
t <sub>on</sub>	turn-on time			-	-	70	ns
t <sub>s</sub>	storage time			-	-	200	ns
t <sub>f</sub>	fall time			-	-	50	ns
t <sub>off</sub>	turn-off time			-	-	250	ns
C <sub>c</sub>	collector capacitance	$V_{CB} = 5 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	-	4	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 500 \text{ mV};$ $I_C = i_c = 0 \text{ A}; \text{ f} = 1 \text{ MHz}$		-	-	8	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 20 V; I <sub>C</sub> = 10 mA; f = 100 MHz		300	-	-	MHz
NF	noise figure			-	-	5	dB

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### 8. Test information



#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



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### **10. Packing information**

Table 8.         Packing methods           The indicated -xxx are the last three digits of the 12NC ordering code.[1]					
Type number	Package	Description	Packing quantity		
			10000		
PMBT3904MB	SOT883B	2 mm pitch, 8 mm tape and reel	-315		
[1] For further in	formation and	I the availability of packing methods, see Section 14.			

### 11. Soldering



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### **12. Revision history**

Table 9. Revision histo	ry			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBT3904MB v.1	20120307	Product data sheet	-	-

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### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Date of release: 7 March 2012 Document identifier: PMBT3904MB\_1

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